NSN 5961-01-304-5479

Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:
Glass
Overall Length:
Between 0.150 inches and 0.170 inches
Terminal Length:
Between 1.000 inches and 1.500 inches
Overall Diameter:
Between 0.068 inches and 0.076 inches
End Application:
Avionic support equip and parts
Mounting Method:
Terminal
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
50.0 working peak reverse voltage and 0.135 forward voltage, dc and 0.175 forward voltage, dc
Current Rating Per Characteristic:
200.00 nanoamperes forward current, average peak
Power Rating Per Characteristic:
250.0 milliwatts small-signal input power, common-collector preset
Capacitance Rating In Picofarads:
2.0
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius ambient air
Special Test Features:
Fwd voltage as described
Test Data Document:
30003-1058as341 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) and
81349-mil-prf-19500/444 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in
specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on
certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig:
A110a0

Mil-prf-19500 spec.

Mil-std (military Standard):